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107. A method according to claim 29, further comprising a step of removing the porous layer remaining on the transferred semiconductor layer.

108. A method according to claim 29, further comprising a step of forming an electrode on the transferred semiconductor layer.

109. A method according to claim 29, further comprising a step of introducing an impurity into the transferred semiconductor layer.

110. A method according to claim 29, further comprising a step of forming a semiconductor layer containing an impurity on the transferred semiconductor layer.--

Remarks

The claims are 1-3, 5-8, 10-23, 25-67 and 82-110, with claims 1, 21, 29, 52, 57, 82 and 85 being independent. Claims 4, 9, 24 and 68-81 have been cancelled without prejudice. Claims 1, 21, 29, 34, 41 and 42 have been amended. New claims 87-110 have been added. Reconsideration of the present claims is respectfully requested.


The specification has been amended in order to correct minor errors and to be consistent with the parent application to this divisional case.

Claims 1, 21, 29, 34, 41 and 42 have been amended. Claims 1 and 21 have been amended to incorporate the limitations of cancelled claims 4 and 24, respectively. Claim 29 has been rewritten in independent form. Claims 34, 41 and 42 have been amended to correct typographical errors. No new matter has been added.

New claims 87-110 have been added. Each of these claims depend ultimately from newly independent claim 29 and correspond to original claims 22, 23, 25-28 and 30-47, respectively. No new matter has been added.

Applicants' undersigned attorney may be reached in our New York office by telephone at (212) 218-2100. All correspondence should continue to be directed to our below listed address.

Respectfully submitted,


Attorney for Applicants
Registration No. 42,607

FITZPATRICK, CELLA, HARPER & SCINTO
30 Rockefeller Plaza
New York, New York 10112-3801
Facsimile: (212) 218-2200